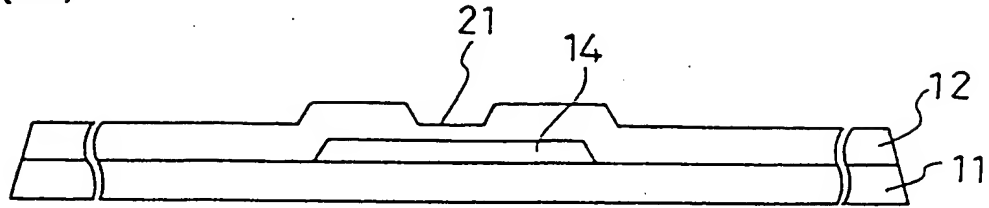
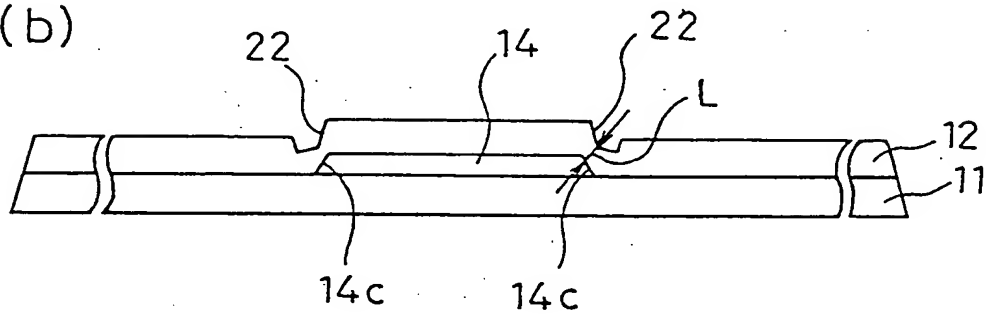


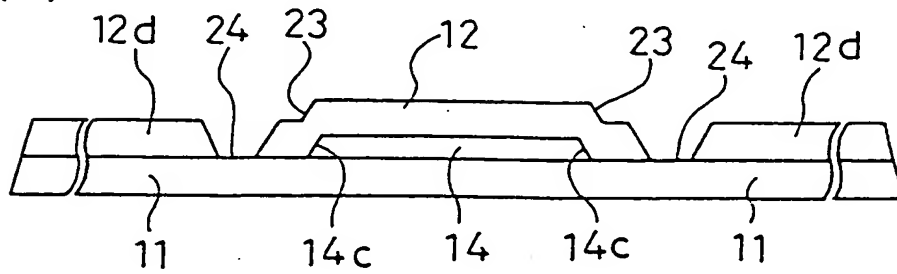
(a)



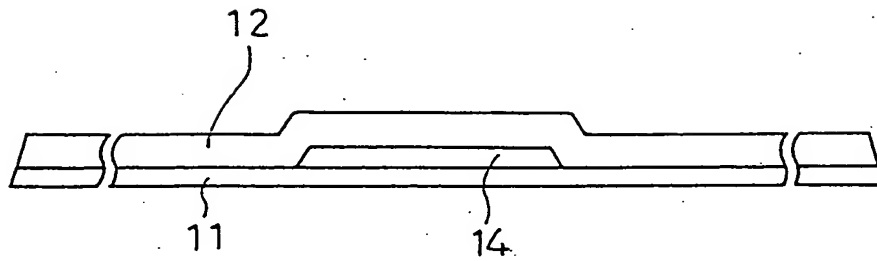
(b)



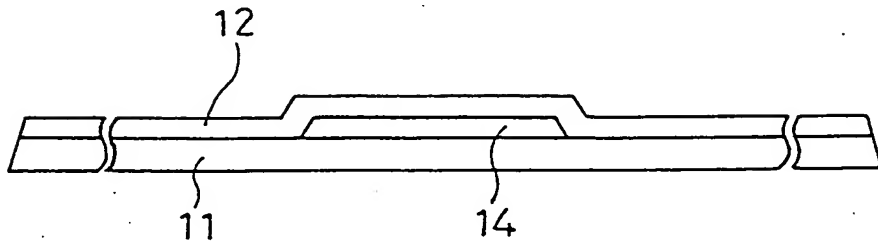
(c)



(a)



(b)



A cross-sectional view of a semiconductor device. A central channel 11 is formed in a substrate 14. A gate 12g is positioned above the channel. The channel has a width $W1$ and the substrate has a thickness $W2$. Arrows indicate a potential gradient ∇b across the channel.

FIG. 6

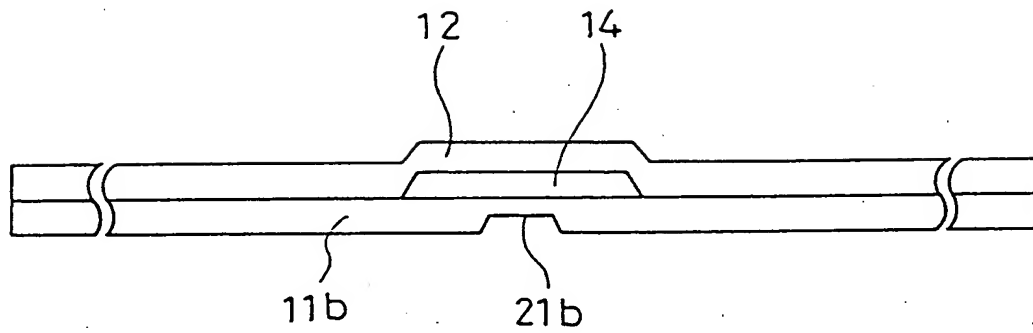
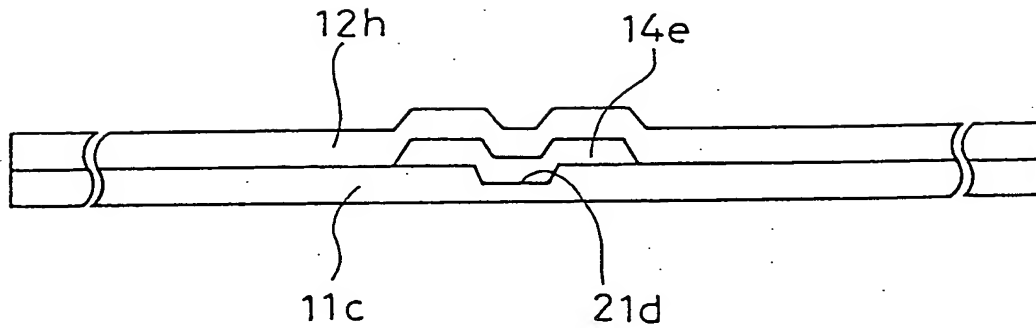
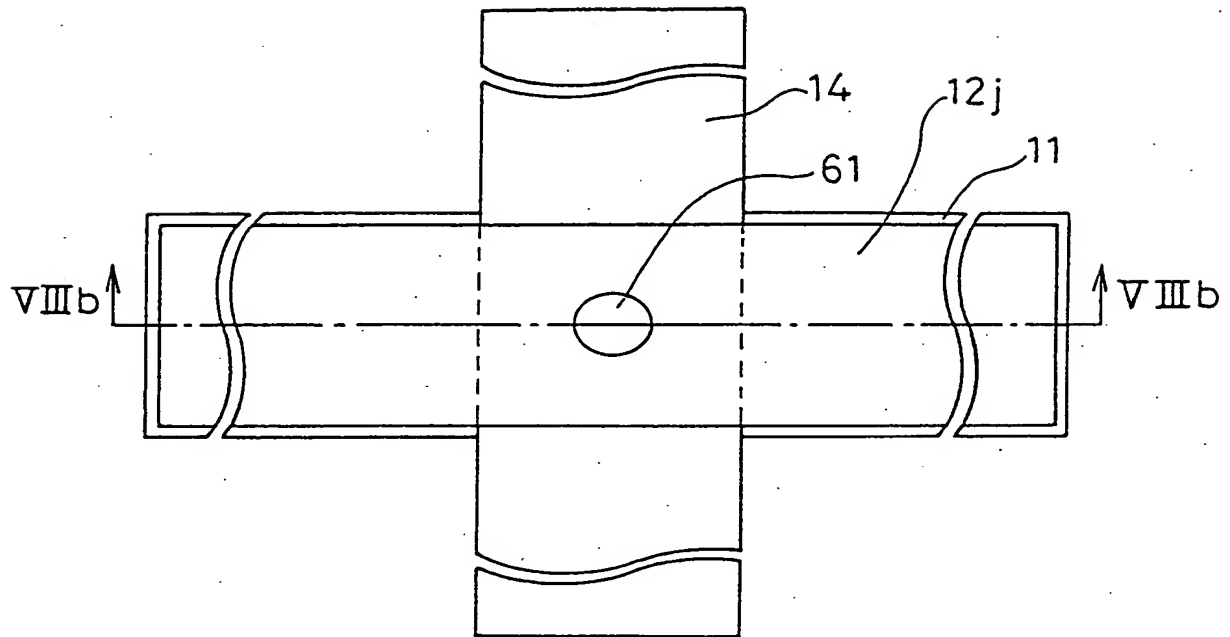


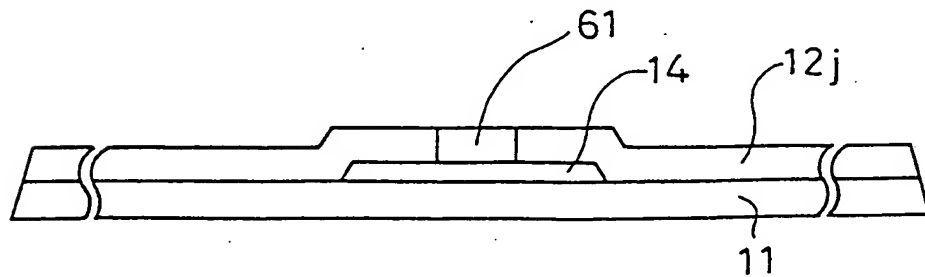
FIG. 7



(a)



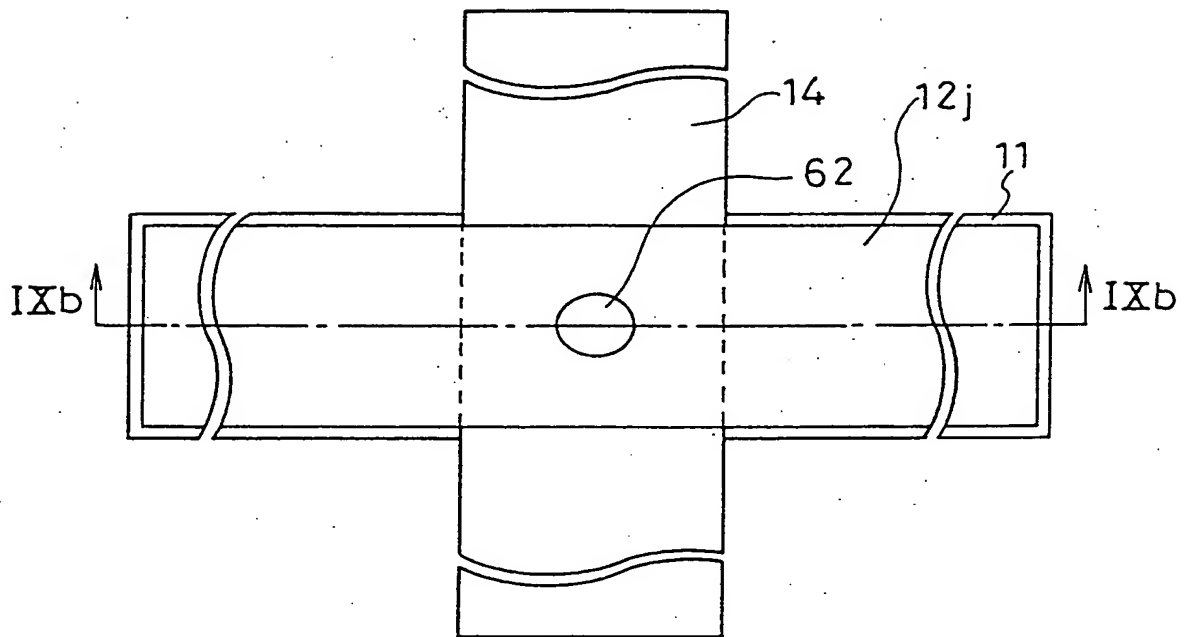
(b)



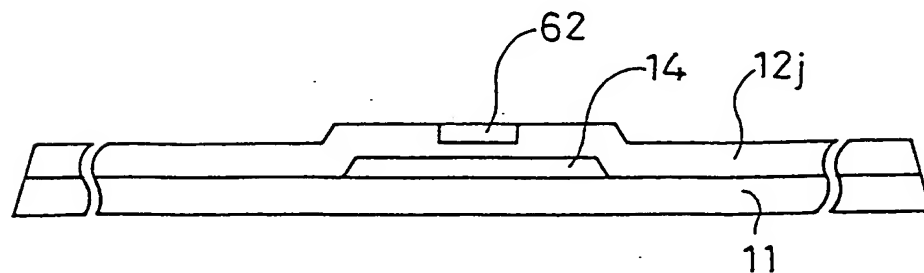
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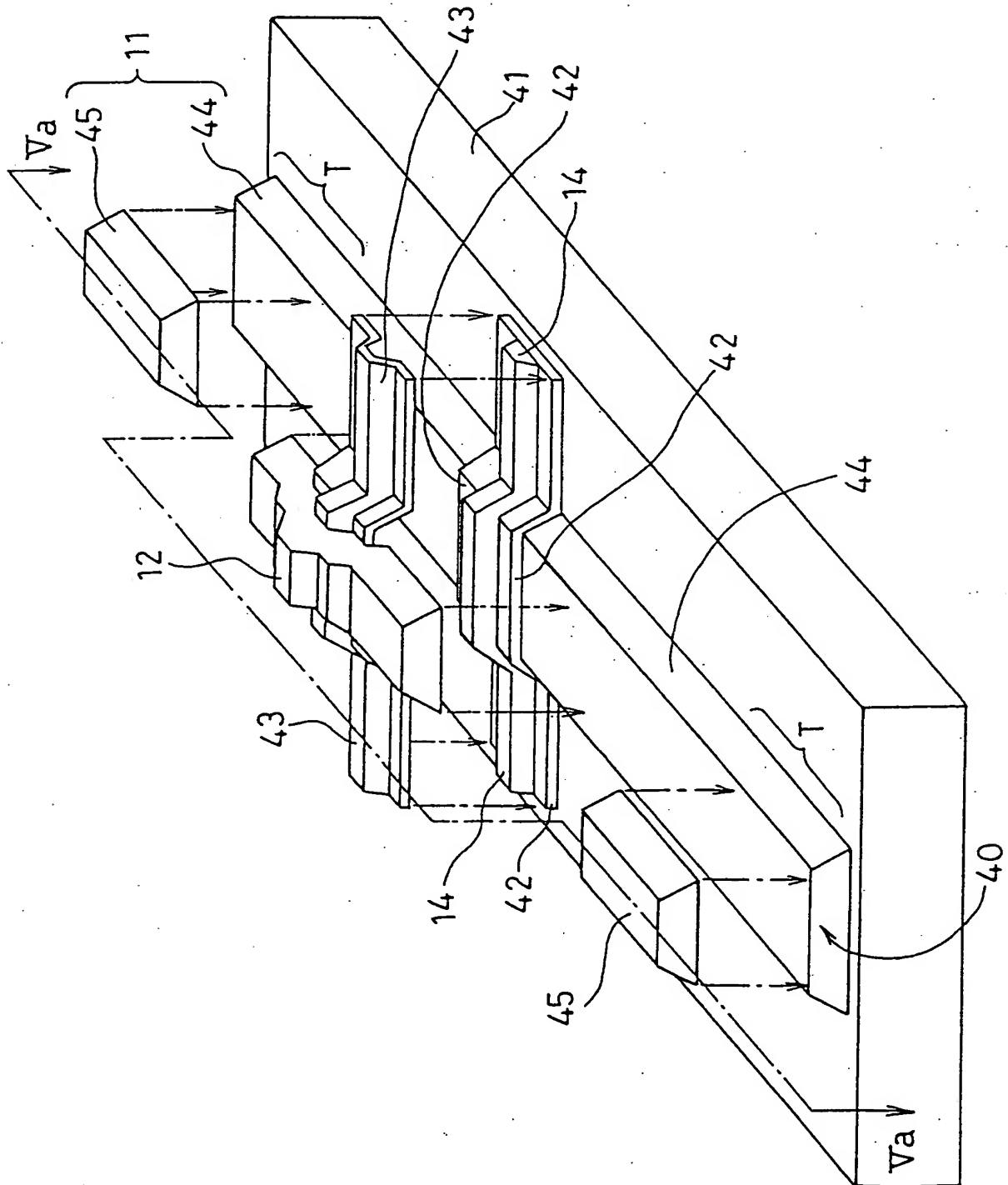
FIG. 9

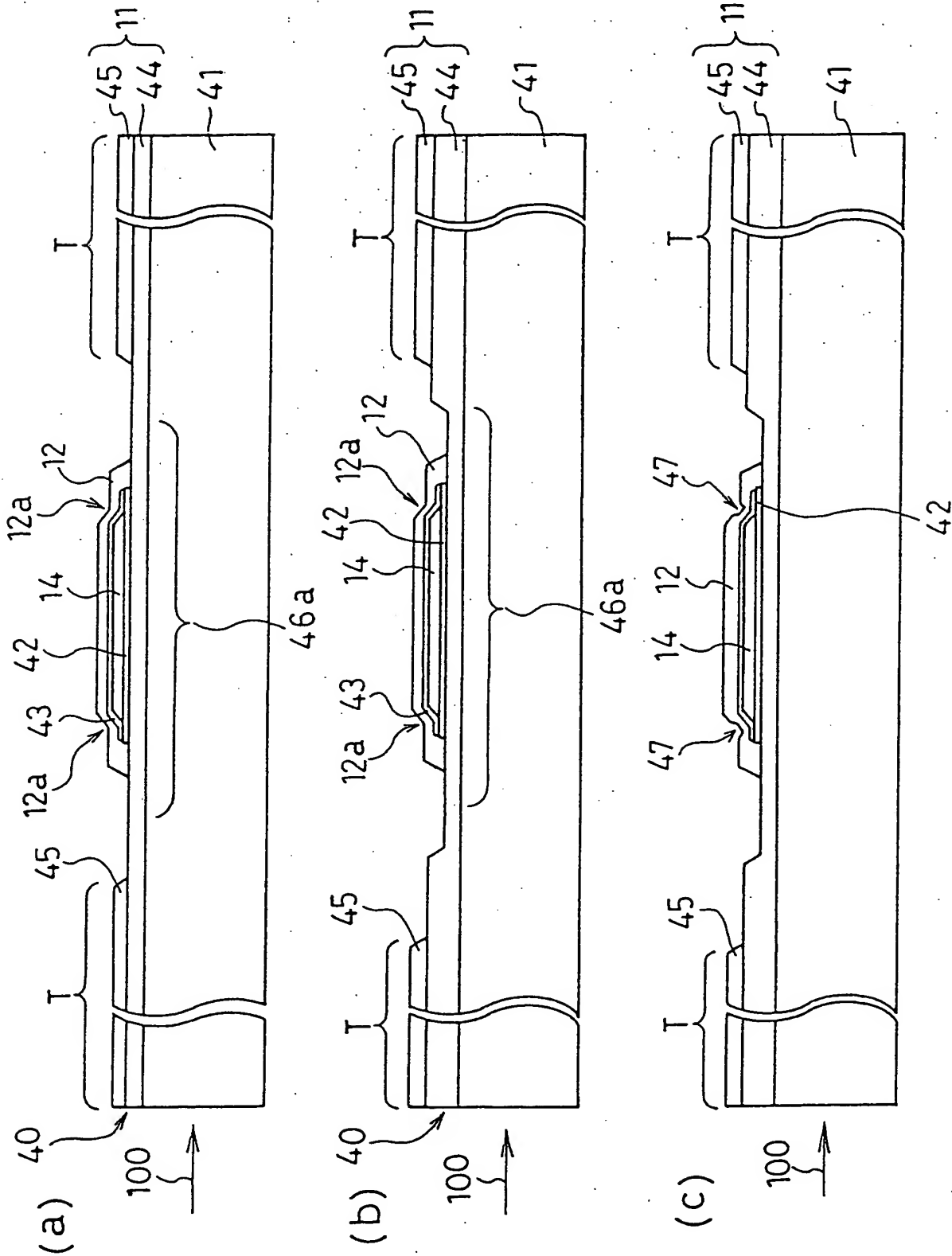
(a)

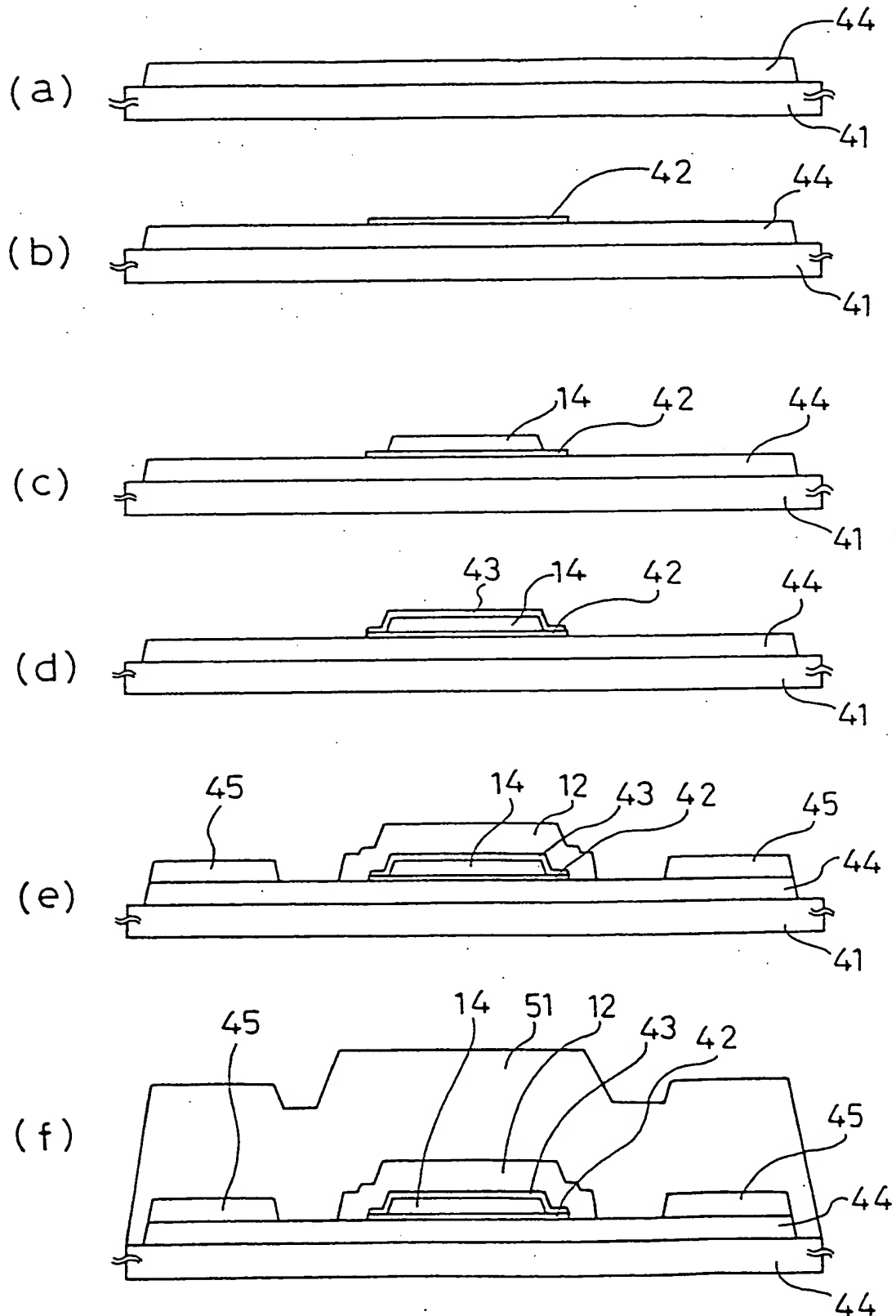


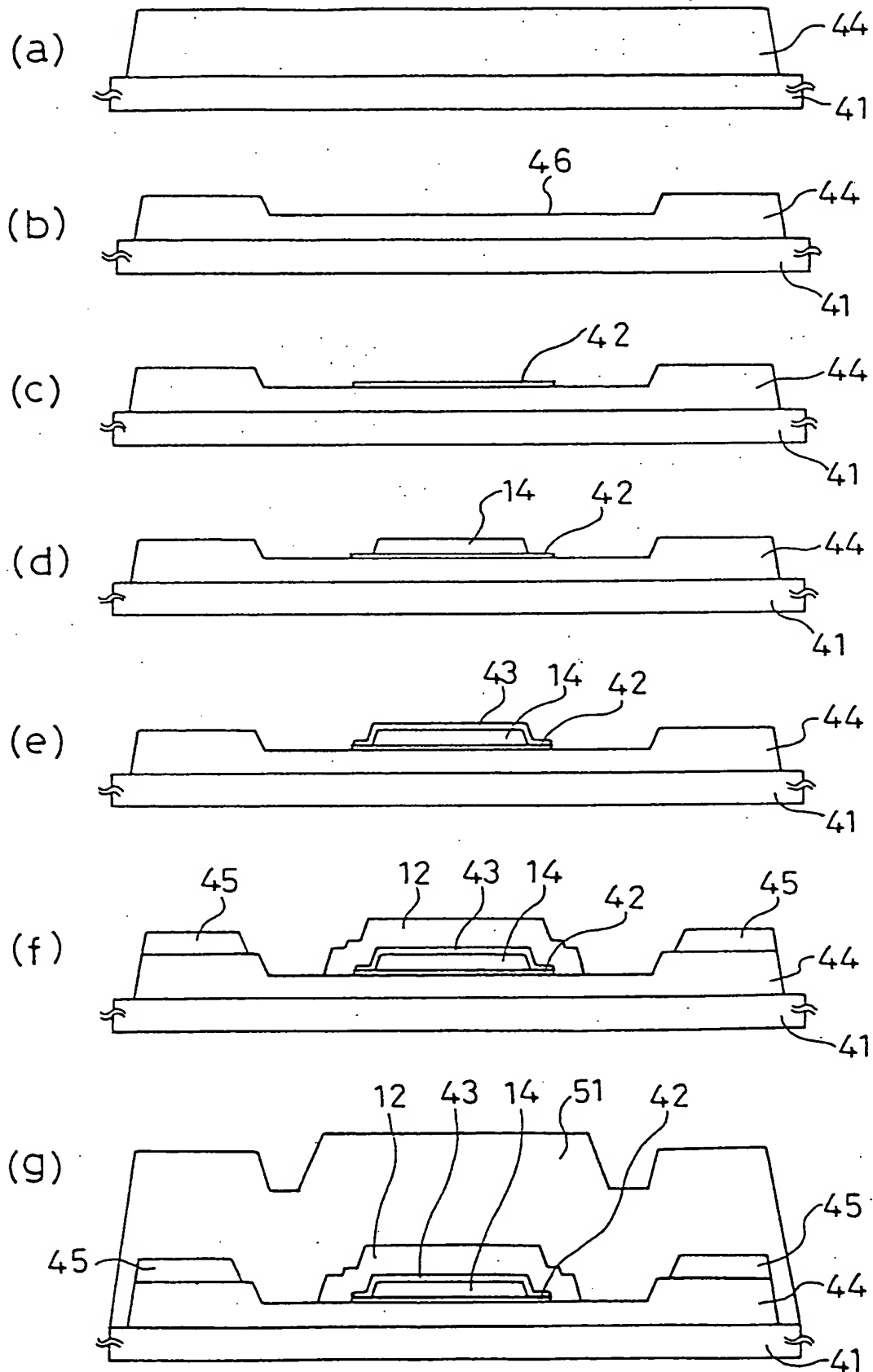
(b)

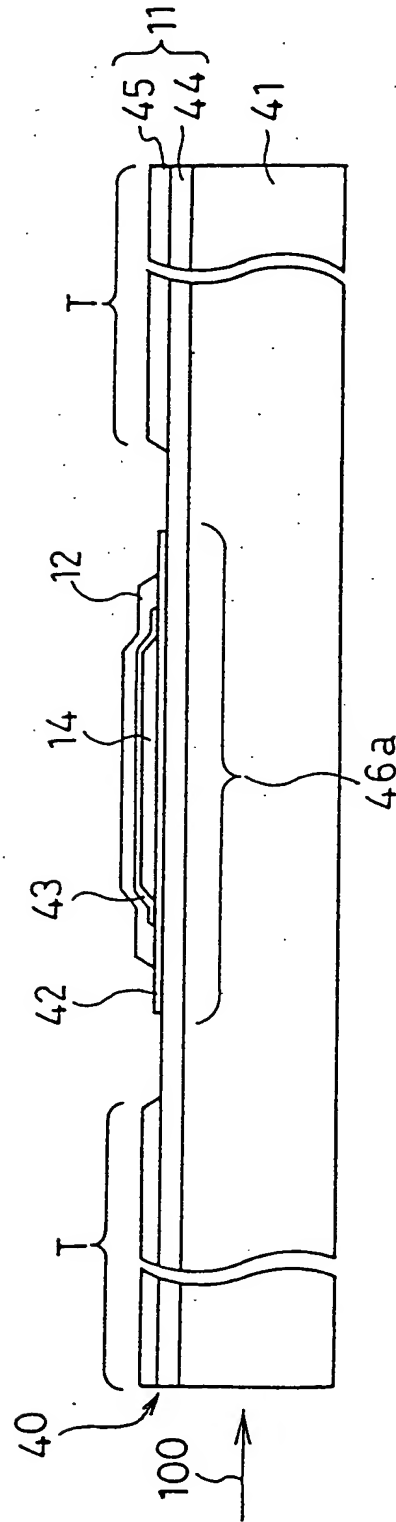












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FIG. 15

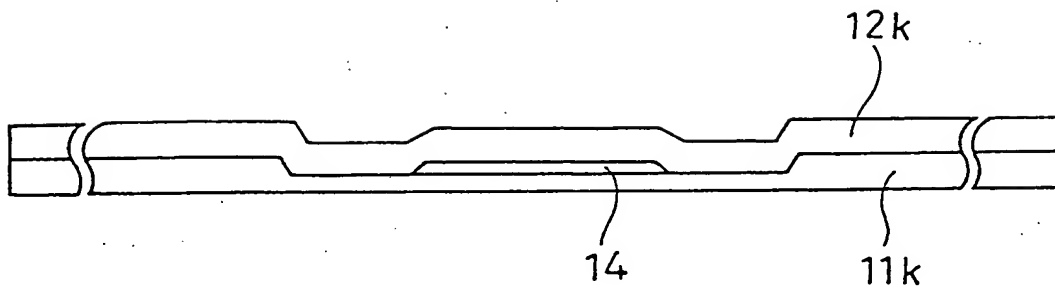
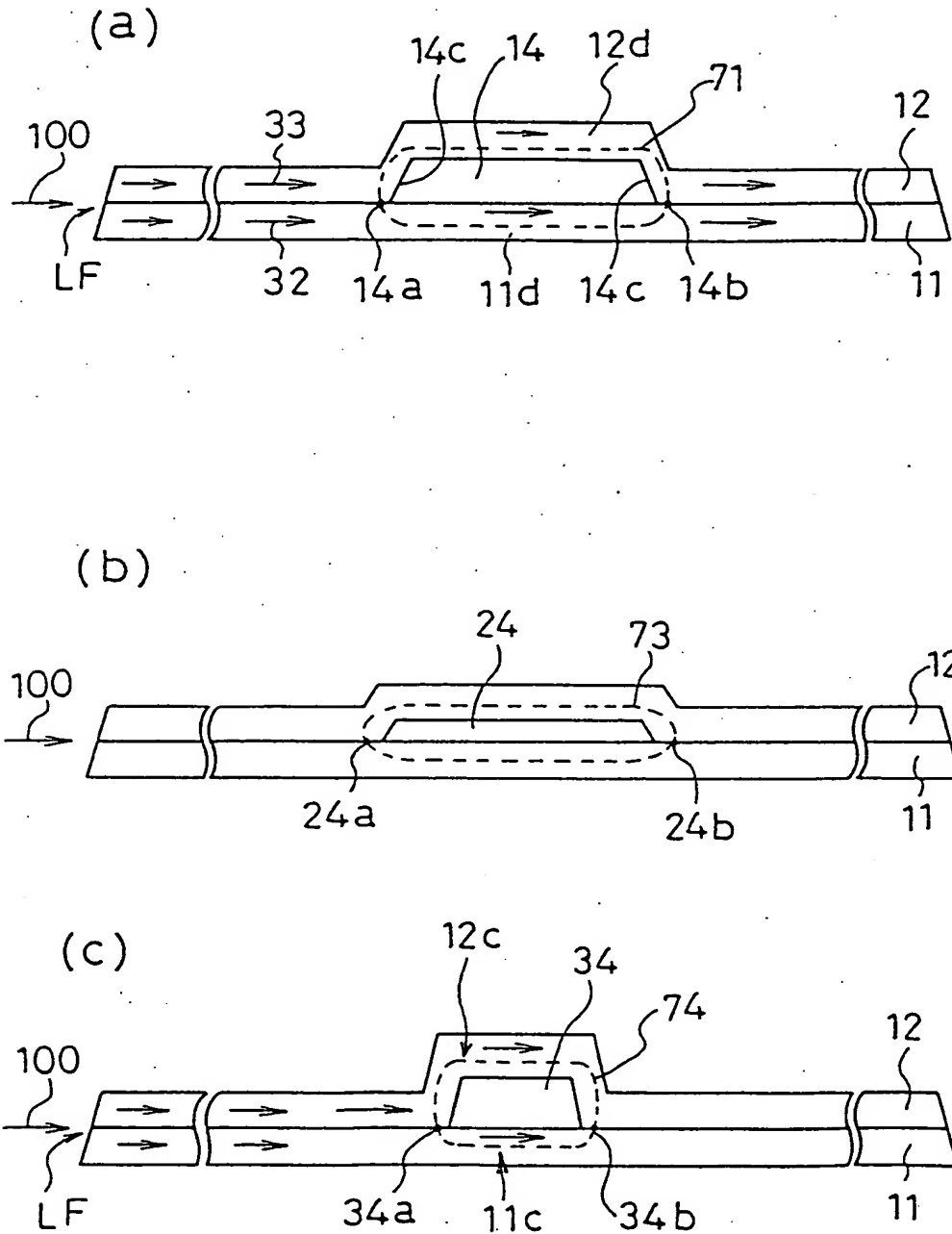


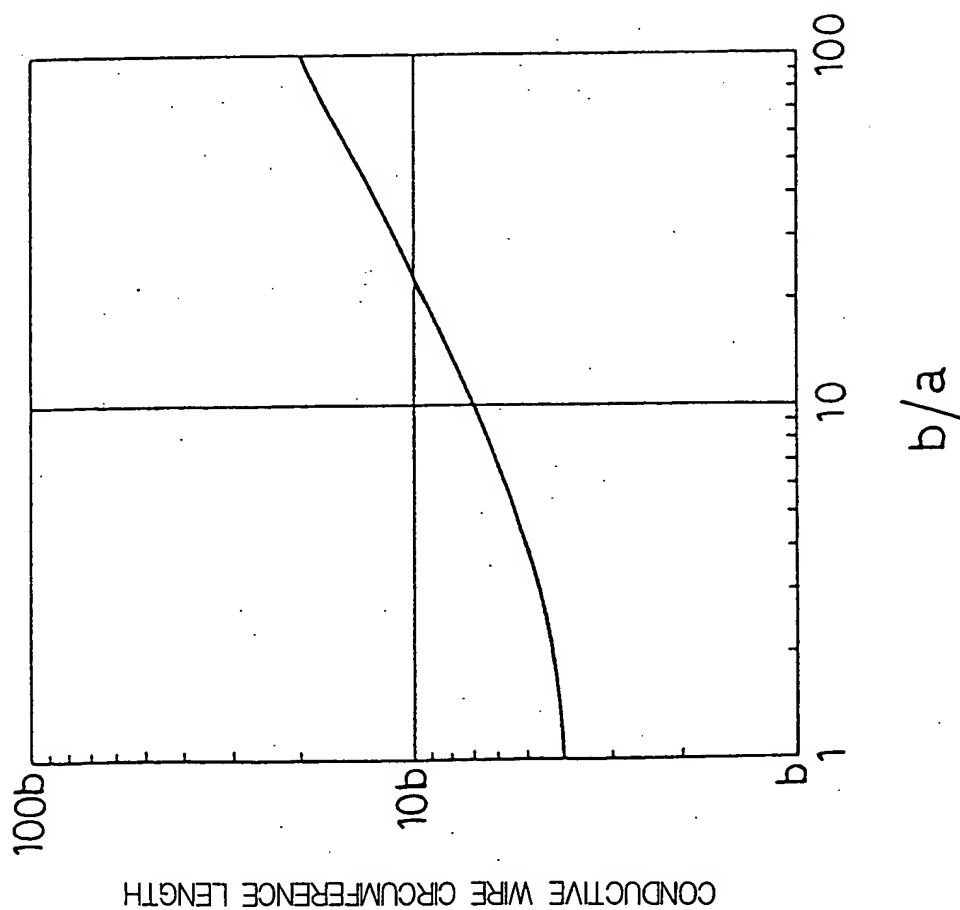
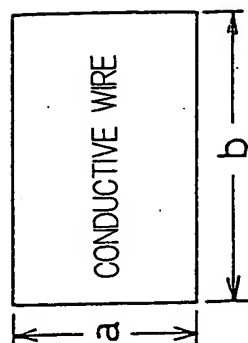
FIG. 16



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FIG. 17



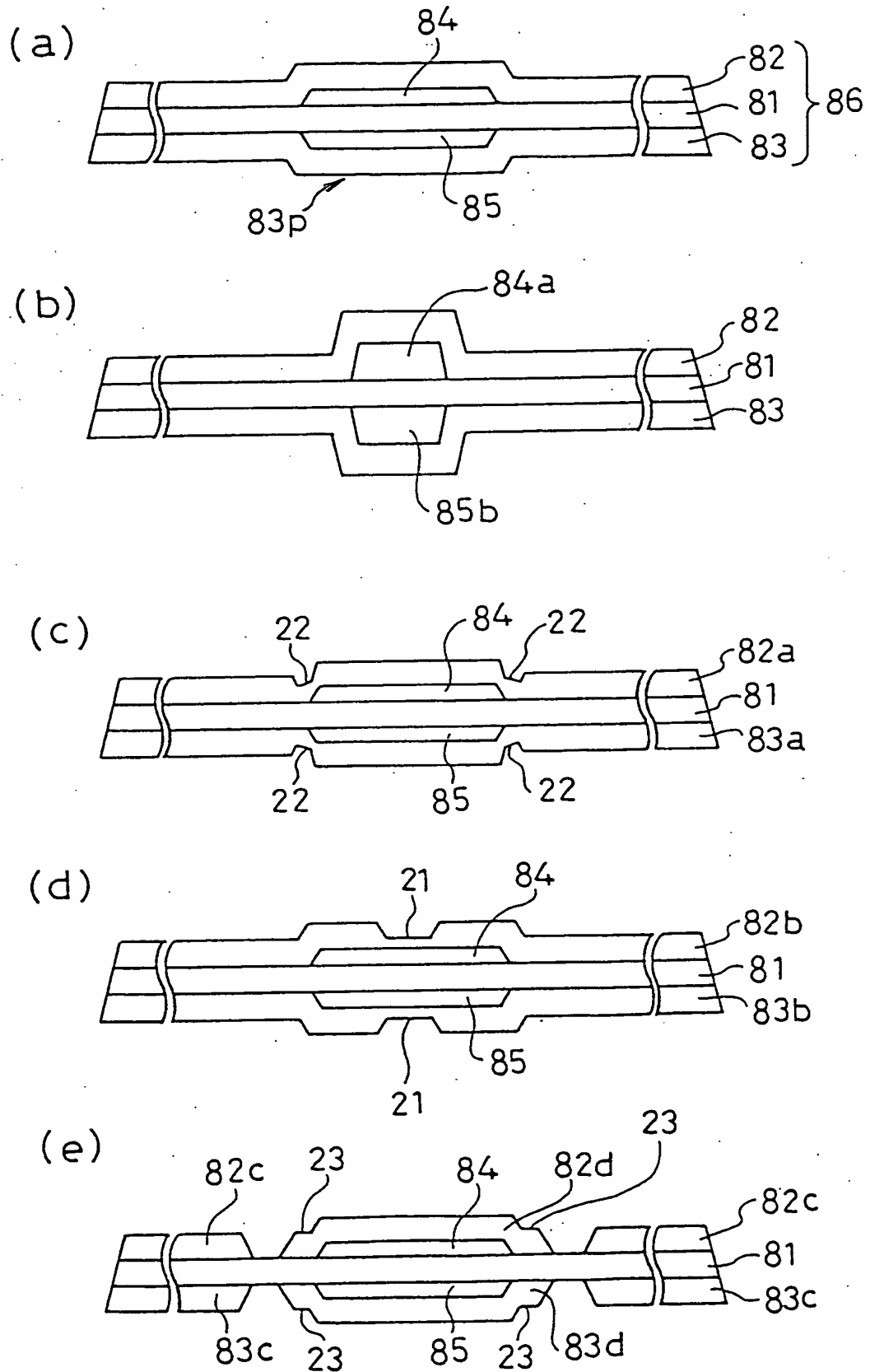
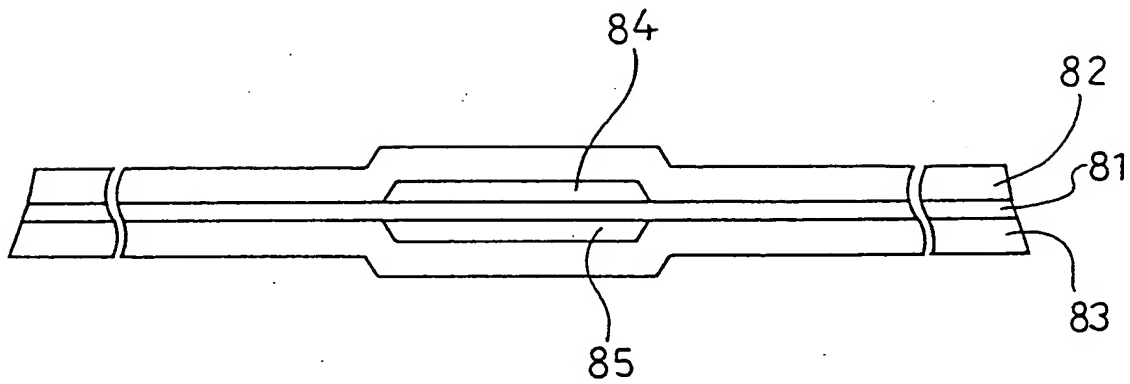
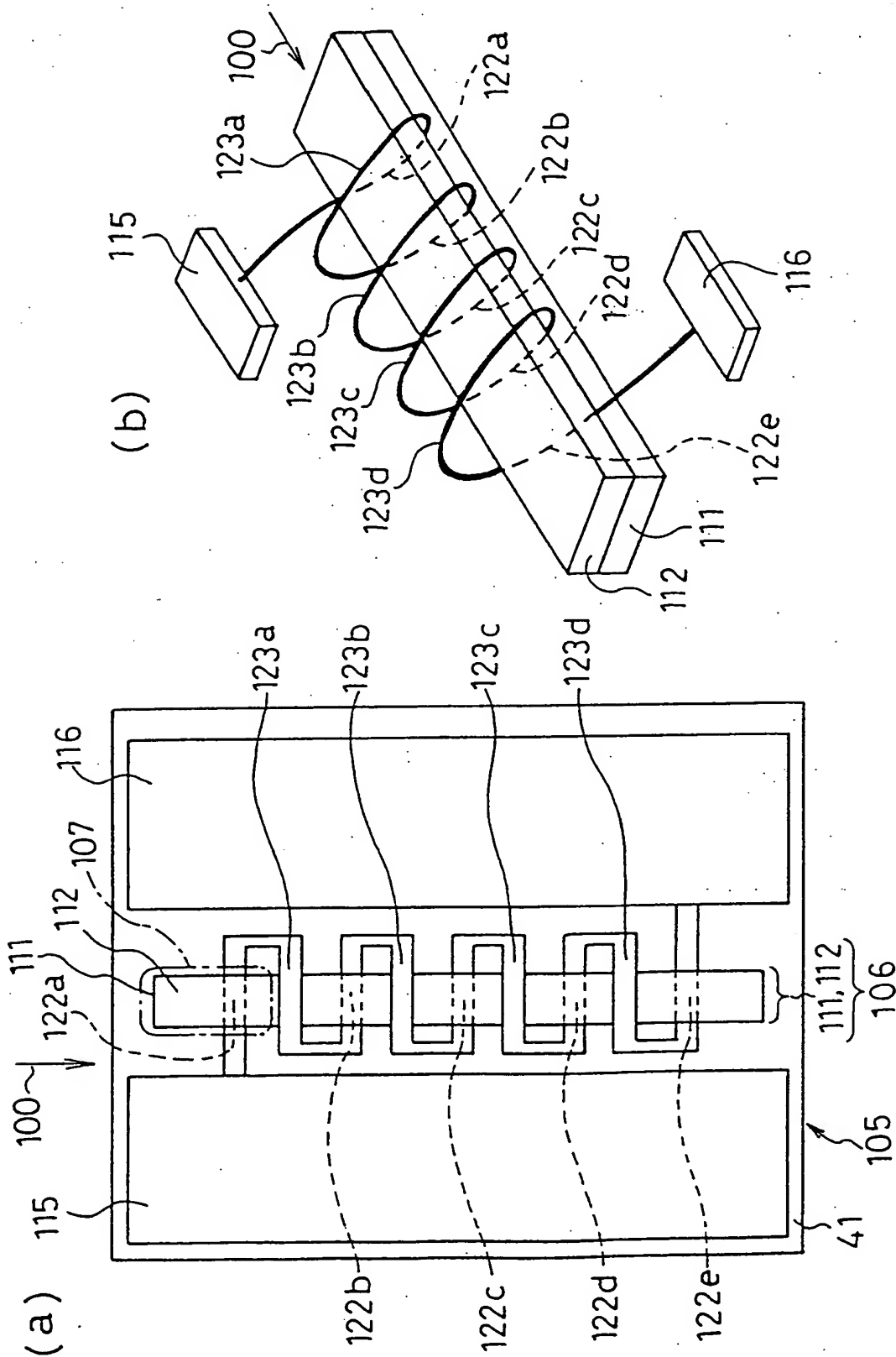
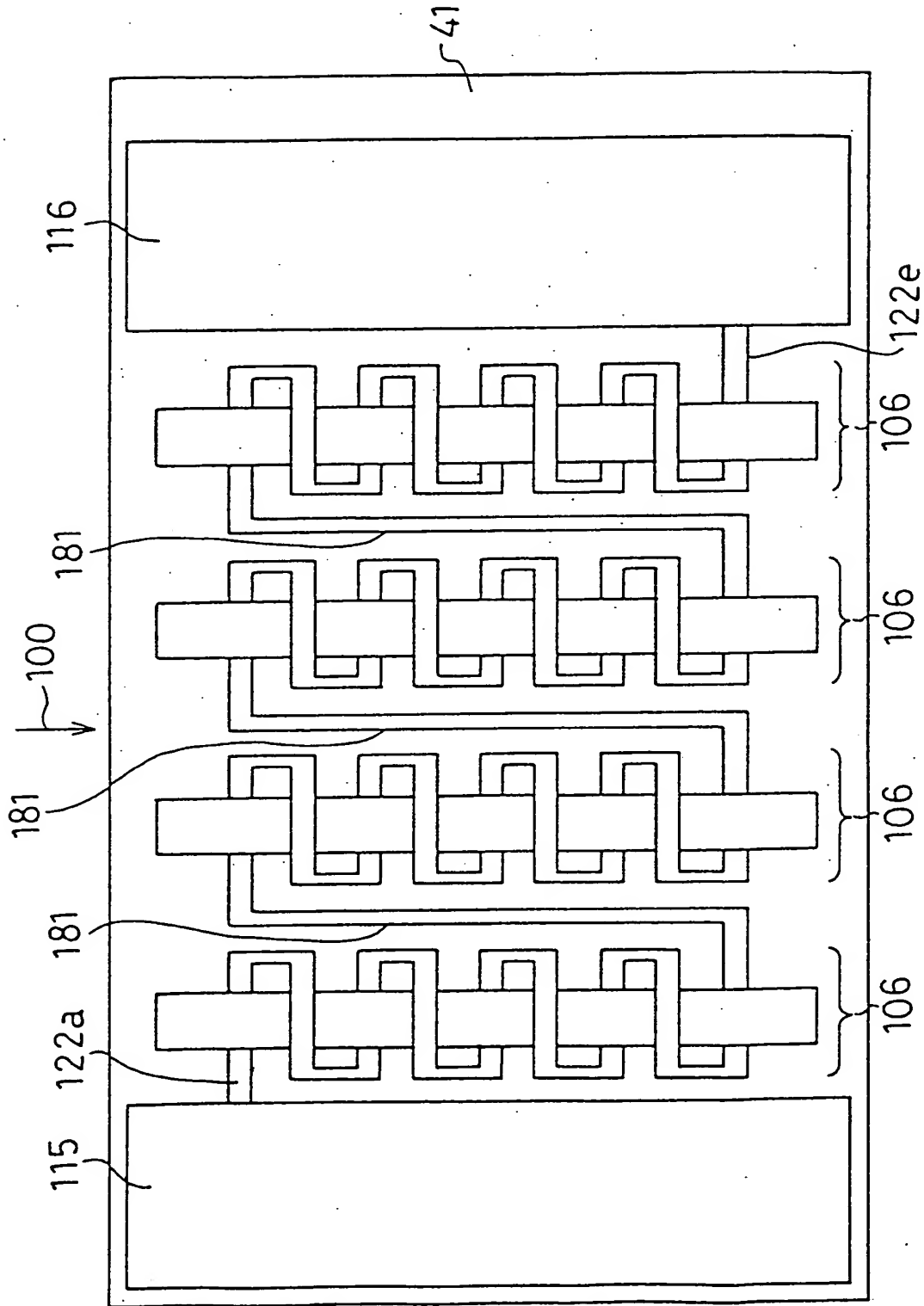
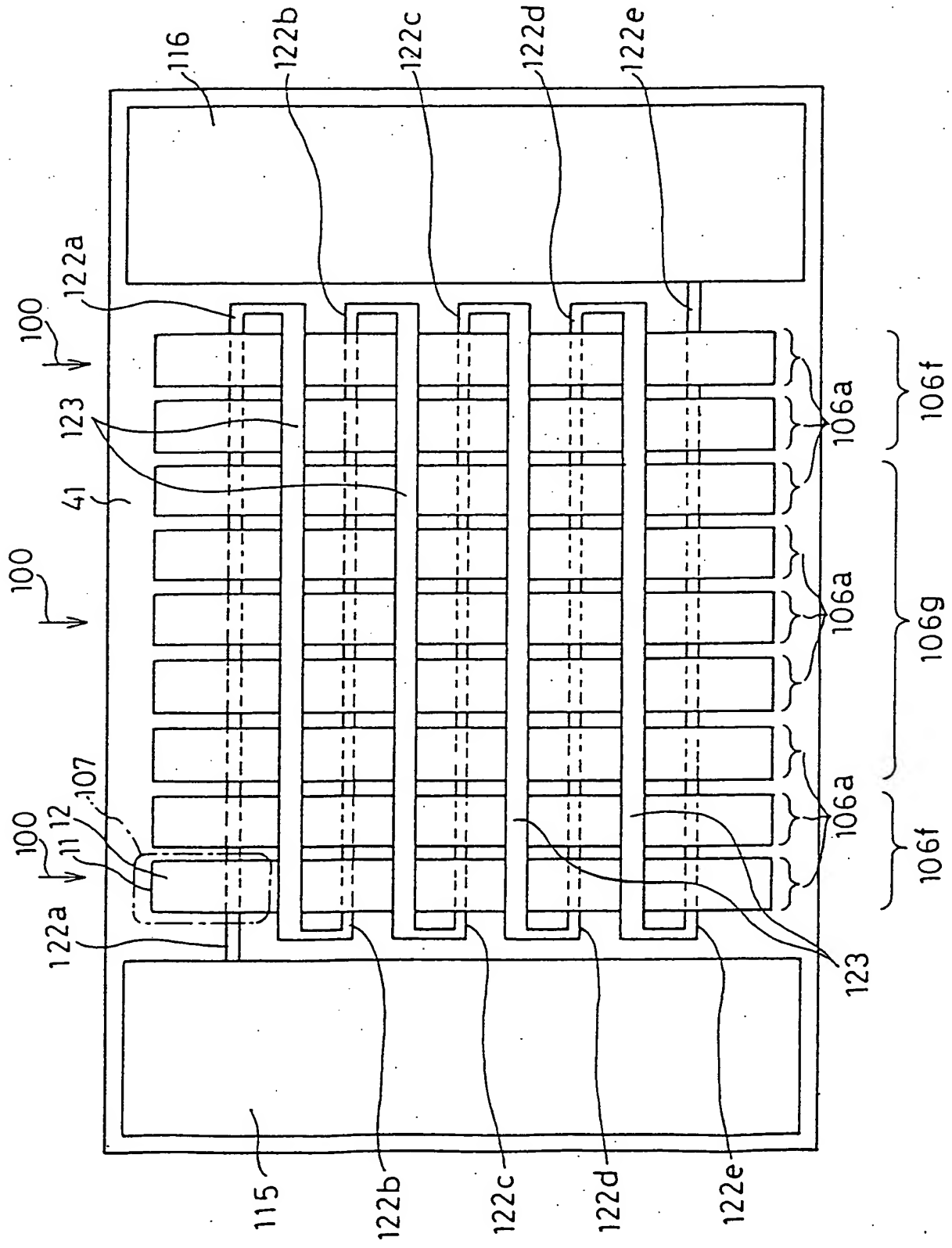


FIG. 20





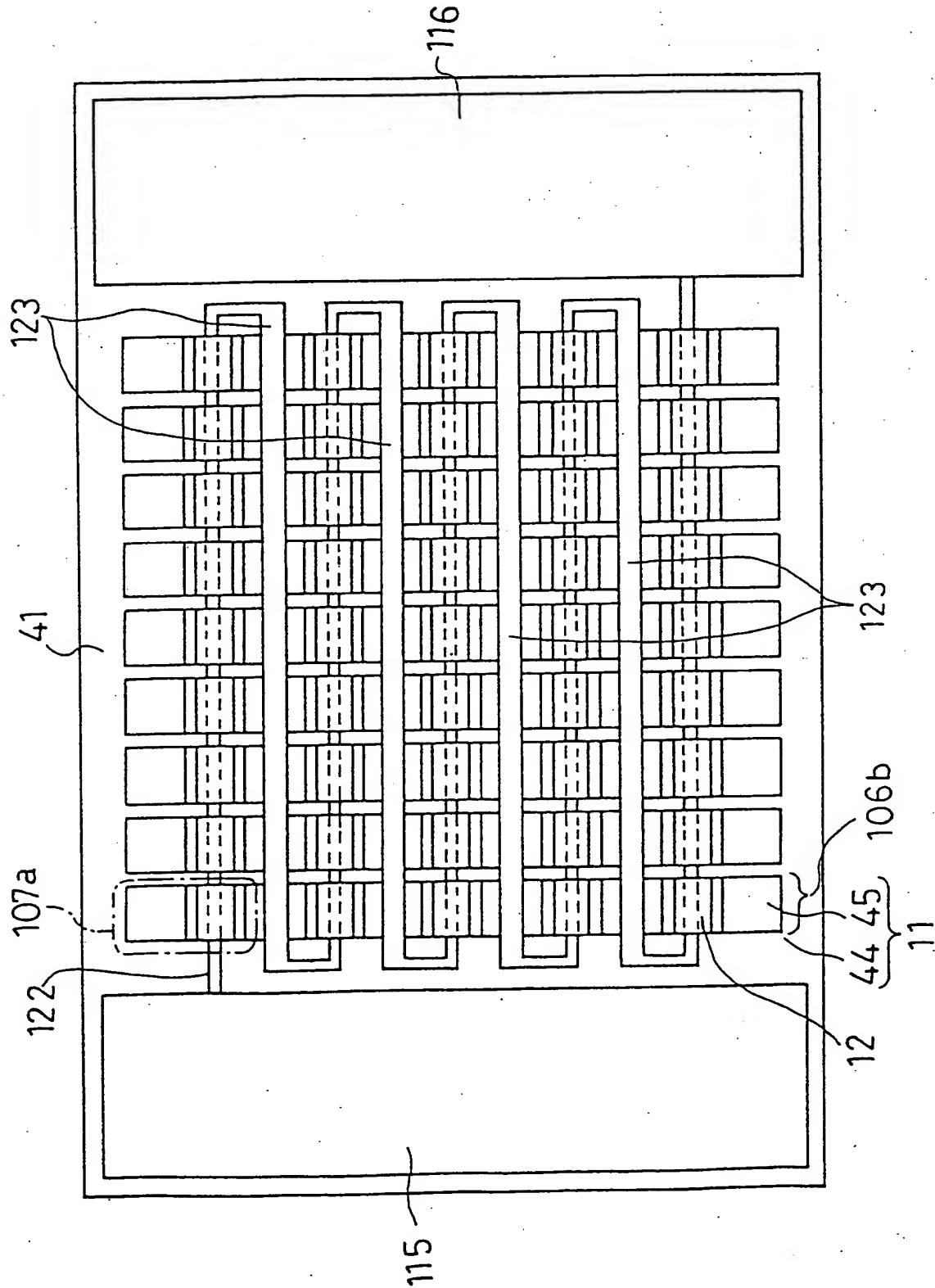


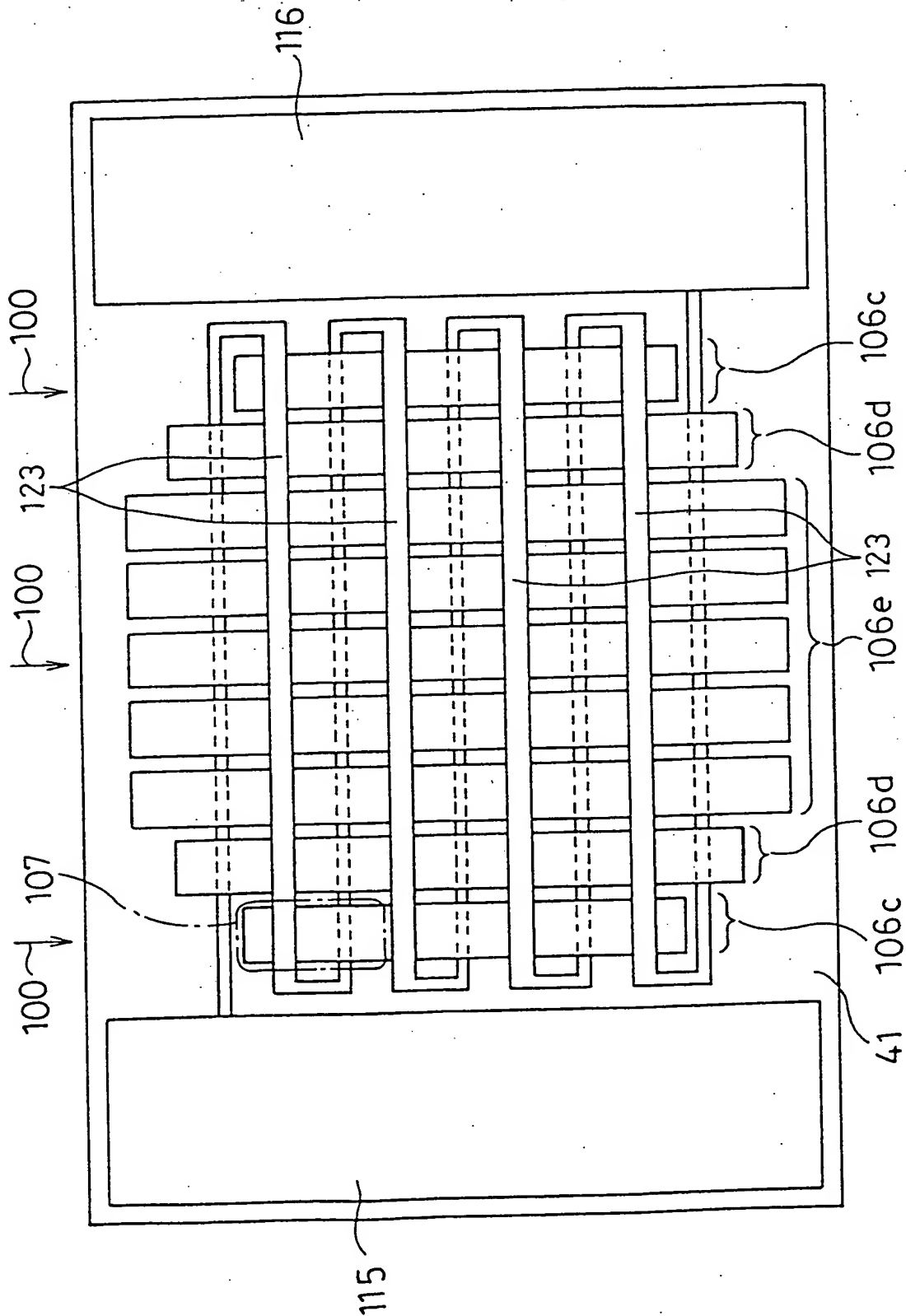


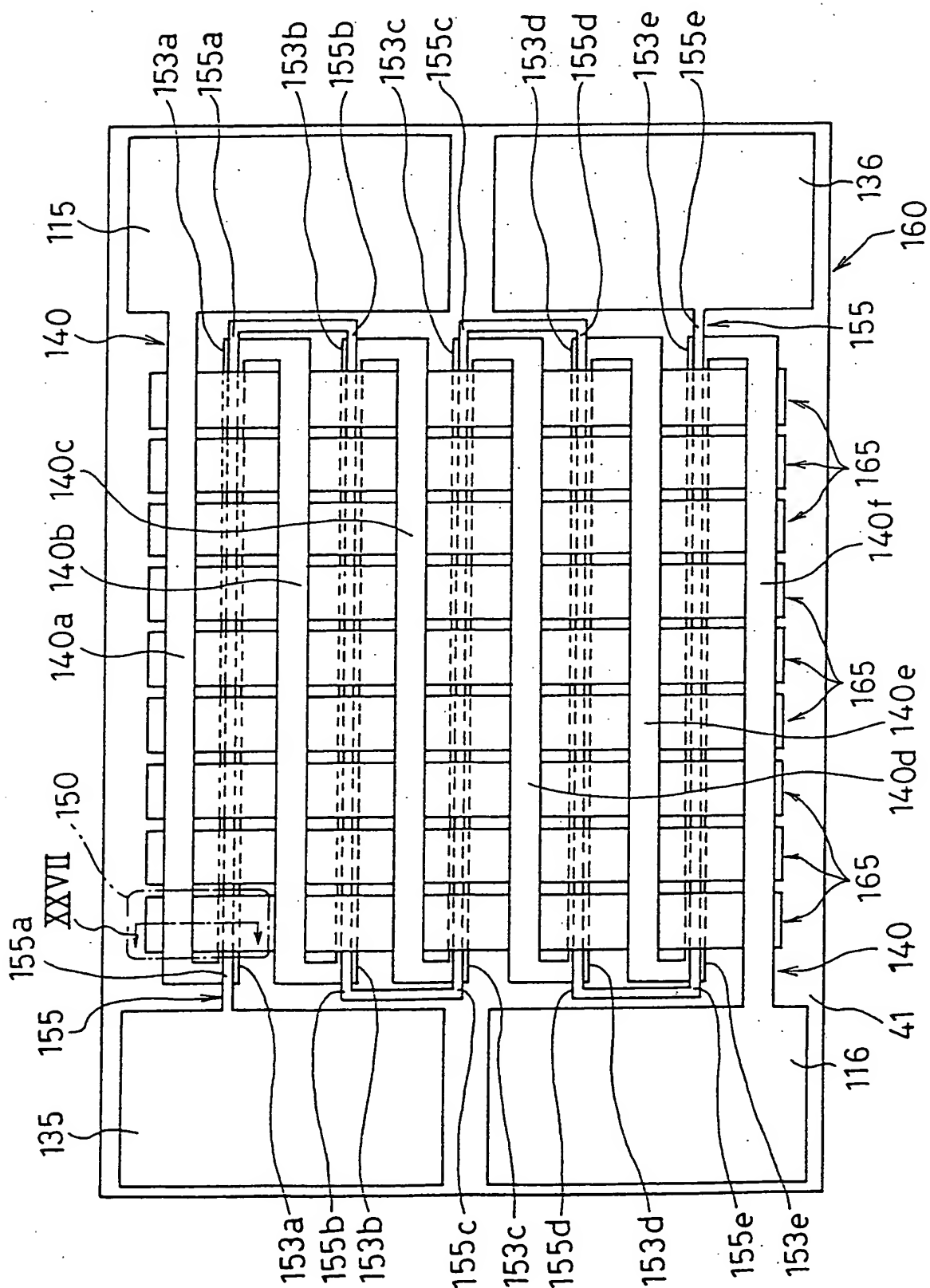
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FIG. 24







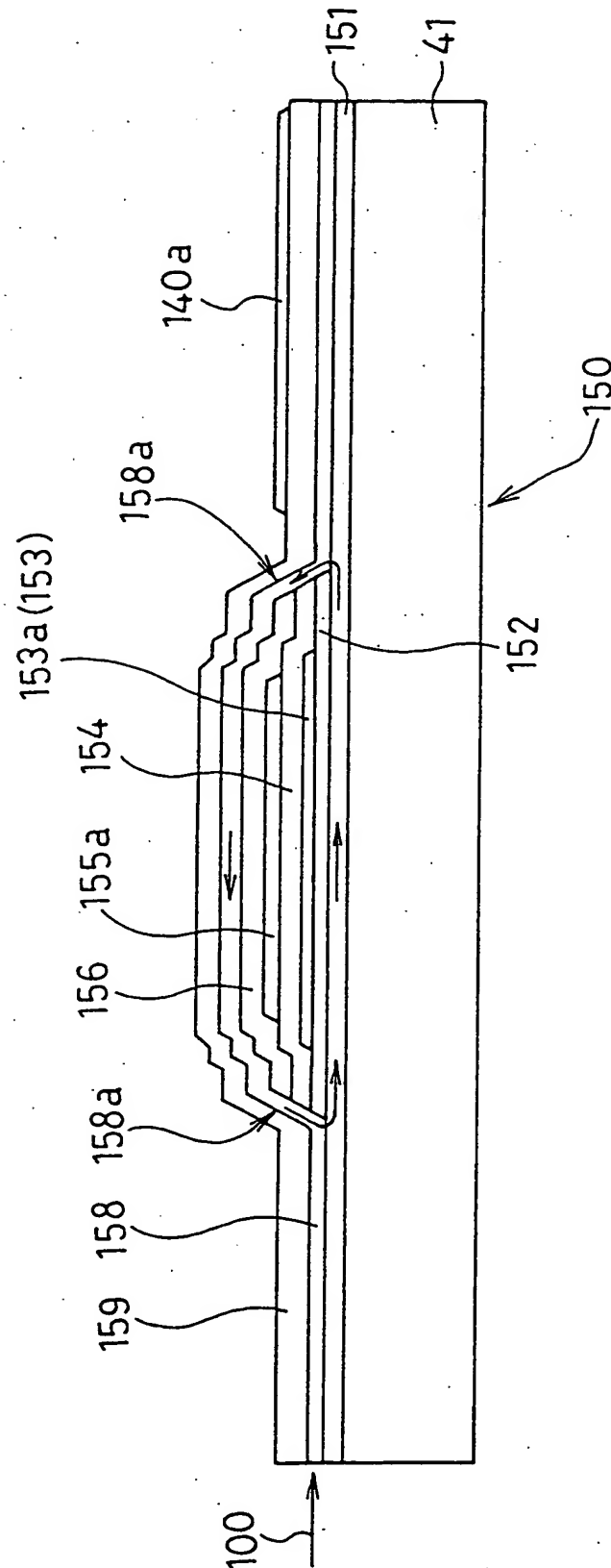


FIG. 28

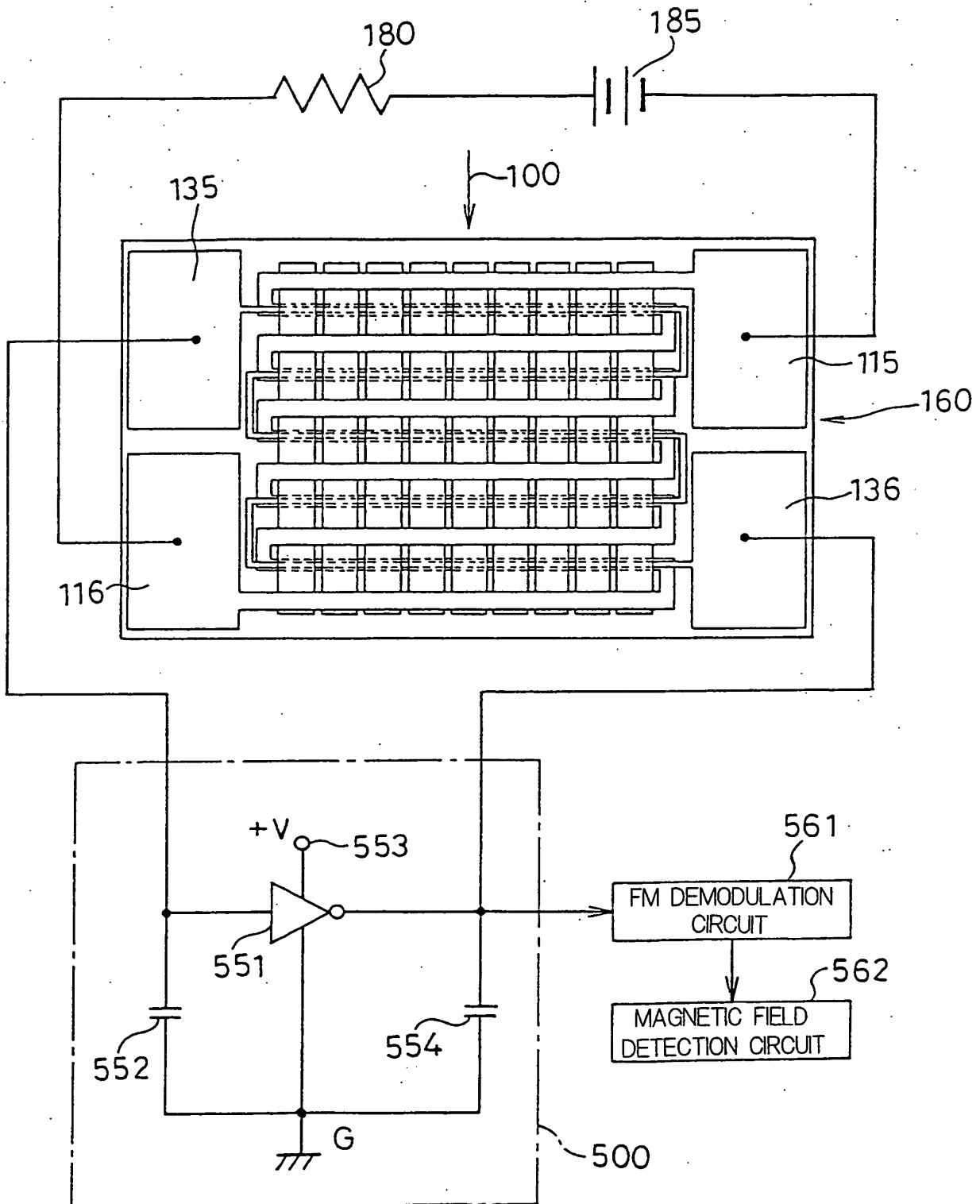


FIG. 29

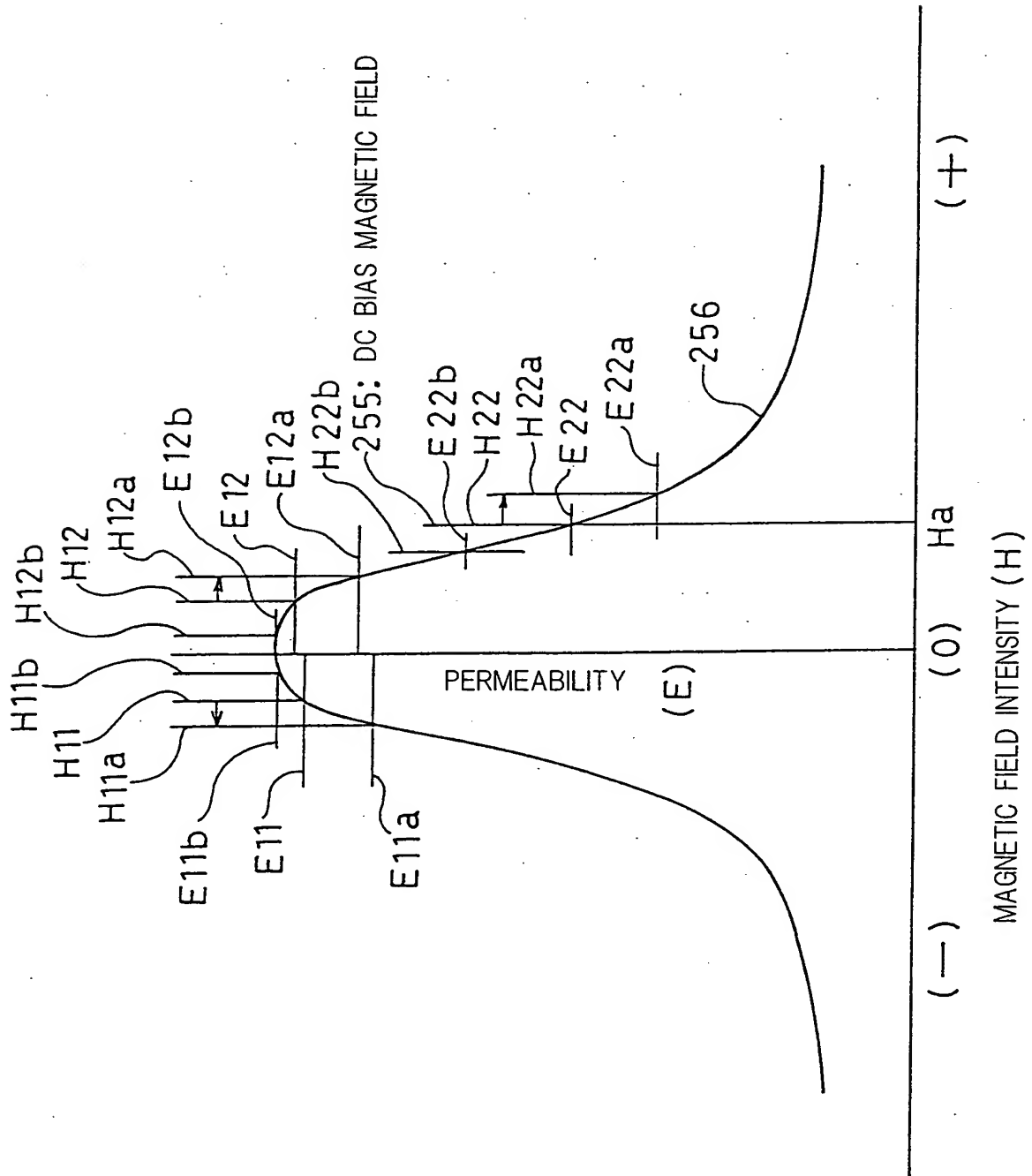
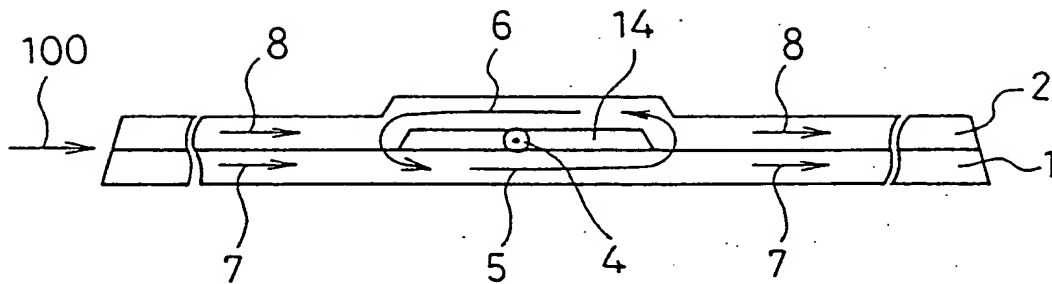
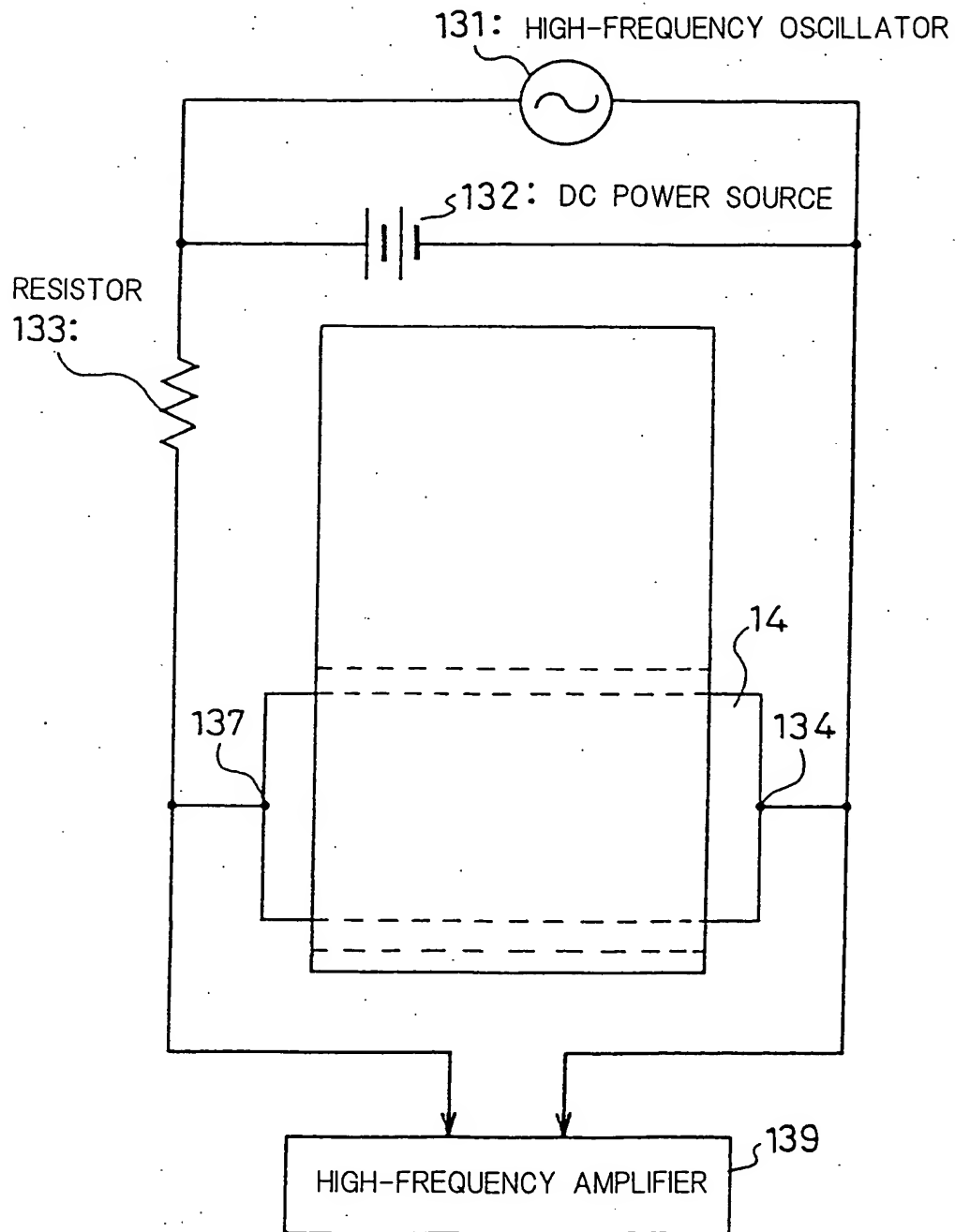


FIG. 30





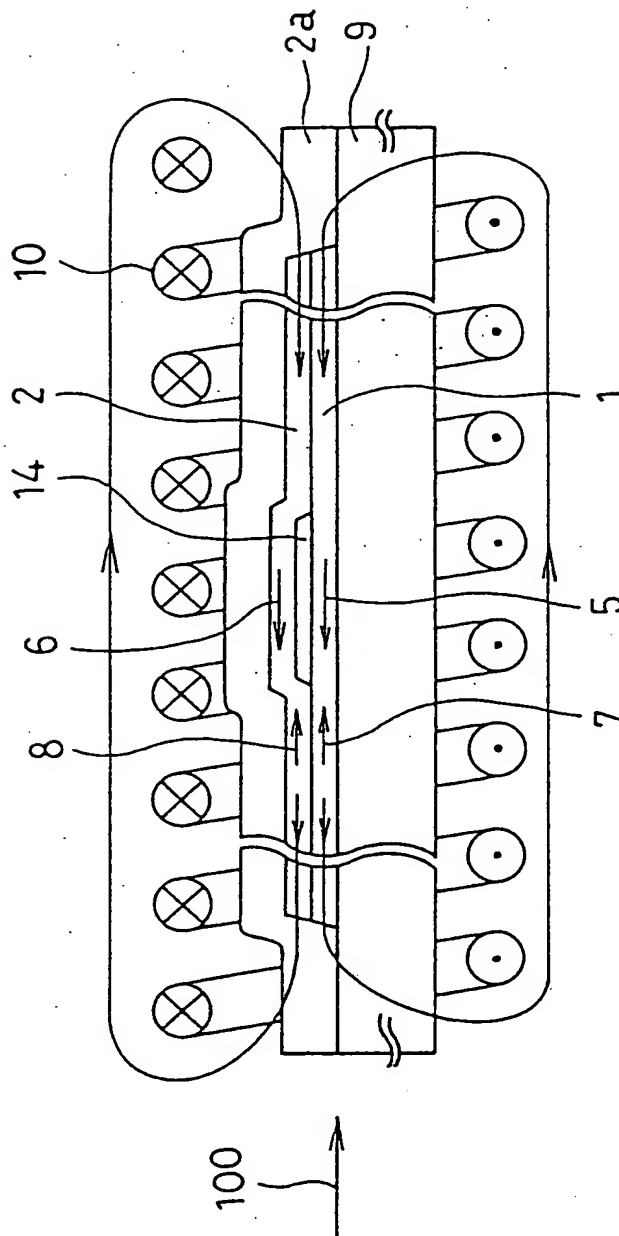


FIG. 33

